

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A light-emitting transistor, ~~which is characterized in that it comprises:~~ comprising:

- a) a gate electrode covered with an insulating film;
- b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;
- c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 ~~electron-volts;~~ electron-volts, the second source/drain electrode including an adhesive base layer made of the electron-injecting material and entirely covered with the hole-injecting material; and
- d) a light-emitter layer provided on the insulating film between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

2-4. (Canceled)

5. (Currently Amended) The light-emitting transistor according to claim 1, ~~which is characterized in that~~ wherein the electron-injecting material is aluminum, magnesium, calcium, magnesium-silver alloy, or a combination of two or more of these materials.

6. (Currently Amended) The light-emitting transistor according to claim 1, ~~which is characterized in that~~ wherein the hole-injecting material is gold, platinum, indium tin oxide, chromium, nickel or a combination of two or more of these materials.

7. (Currently Amended) The light-emitting transistor according to claim 1, ~~which is characterized in that~~ wherein the light-emitter layer includes a light emitter in which a material of an area that is in contact with the first source/drain electrode is different from that of

another area that is in contact with the second source/drain electrode, and the area on the side of the first source/drain electrode is made of an electron transport material and the area on the side of the first source/drain electrode is made of a hole transport material.

8. (Currently Amended) The light-emitting transistor according to claim 1, ~~which is characterized in that~~ wherein the thickness of the insulating film satisfies ~~a condition for an interference condition for an emission wavelength of the light emitter layer.~~

9. (Currently Amended) A laser light source, ~~which is characterized in that it comprises:~~ comprising:

- a) a gate electrode covered with an insulating film;
- b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;
- c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 ~~electron-volts;~~ electron-volts, the second source/drain electrode including an adhesive base layer made of the electron-injecting material and entirely covered with the hole-injecting material;
- d) a light-emitter layer provided between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor; and
- e) a diffraction grating provided between the first source/drain electrode and the second source/drain electrode in order to diffract light emitted from the light-emitter layer.

10. (Currently Amended) The laser light source according to claim 9, ~~which is characterized in that~~ wherein the diffraction grating is formed on the gate electrode between the first source/drain electrode and the second source/drain electrode.

11. (Currently Amended) A laser light source, ~~which is characterized in that it comprises:~~ comprising:

a) a gate electrode covered with an insulating film;

b) a comb-shaped first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;

c) a second source/drain electrode, consisting of a comb-shaped electrode made of a hole-injecting material whose work function is higher than 4.26 electron-volts, which is provided on the insulating film and arranged so that its comb-teeth engage into the comb-teeth of the aforementioned first source/drain electrode to form a diffraction-~~grading~~ grating consisting of said two sets of comb-teeth; and

d) a light-emitter layer provided between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

12. (Canceled)

13 (Currently Amended) A light-emitting transistor, ~~which is characterized in that it comprises:~~ comprising:

a) a gate electrode covered with an insulating film;

b) a first source/drain electrode provided on the insulating film and made by stacking a layer of an electron-injecting material whose work function is equal to or lower than 4.26 electron volts and a layer of a hole-injecting material whose work function is higher than 4.26 electron-volts;

c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made by stacking a layer of the same electron-injecting material and a layer of the same hole-injecting material as the first source/drain electrodes in the same order as the first source/drain electrodes; and

d) a light-emitter layer provided on the insulating film between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

14 (Currently Amended) The light-emitting transistor according to claim 13, ~~which is characterized in that~~ wherein the electron-injecting material is aluminum, magnesium, calcium, magnesium-silver alloy, or a combination of two or more of these materials.

15. (Currently Amended) The light-emitting transistor according to claim 13, ~~which is characterized in that~~ wherein the hole-injecting material is gold, platinum, indium tin oxide, chromium, nickel or a combination of two or more of these materials.

16. (Currently Amended) The light-emitting transistor according to claim 13, ~~which is characterized in that~~ wherein the light-emitting layer includes a light emitter in which a material of an area that is in contact with the first source/drain electrode is different from that of another area that is in contact with the second source/drain electrode, and the area on the side of the first source/drain electrode is made of an electron transport material and the area on the side of the first source/drain electrode is made of a hole transport material.

17. (Currently Amended) The light-emitting transistor according to claim 13, ~~which is characterized in that~~ wherein the thickness of the insulating film satisfies a condition for an interference condition for an emission wavelength of the light emitter layer.

18. (New) A laser light source, comprising:

- a) a gate electrode covered with an insulating film;
- b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;
- c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 electron-volts; the first source/drain electrode including an adhesive base layer made of the hole-injecting material and entirely covered with the electron-injecting material;
- d) a light-emitter layer provided between the first source/drain electrode and the second

source/drain electrode and made of an organic semiconductor; and

e) a diffraction grating provided between the first source/drain electrode and the second source/drain electrode in order to diffract light emitted from the light-emitter layer.

19. (New) The laser light source according to claim 18, wherein the diffraction grating is formed on the gate electrode between the first source/drain electrode and the second source/drain electrode.

20. (New) A light-emitting transistor, comprising:

a) a gate electrode covered with an insulating film;

b) a first source/drain electrode provided on the insulating film and made of an electron-injecting material whose work function is equal to or lower than 4.26 electron-volts;

c) a second source/drain electrode provided separately from the first source/drain electrode on the insulating film and made of a hole-injecting material whose work function is higher than 4.26 electron-volts, the first source/drain electrode including an adhesive base layer made of the hole-injecting material and entirely covered with the electron-injecting material; and

d) a light-emitter layer provided on the insulating film between the first source/drain electrode and the second source/drain electrode and made of an organic semiconductor.

21. (New) The light-emitting transistor according to claim 20, wherein the electron-injecting material is aluminum, magnesium, calcium, magnesium-silver alloy, or a combination of two or more of these materials.

22. (New) The light-emitting transistor according to claim 20, wherein the hole-injecting material is gold, platinum, indium tin oxide, chromium, nickel or a combination of two or more of these materials.

23. (New) The light-emitting transistor according to claim 20, wherein the light-emitter layer includes a light emitter in which a material of an area that is in contact with the

first source/drain electrode is different from that of another area that is in contact with the second source/drain electrode, and the area on the side of the first source/drain electrode is made of an electron transport material and the area on the side of the first source/drain electrode is made of a hole transport material.

24. (New) The light-emitting transistor according to claim 20, wherein the thickness of the insulating film satisfies an interference condition for an emission wavelength of the light-emitter layer.